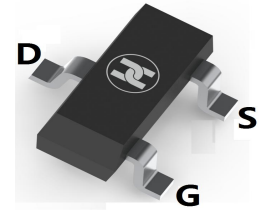
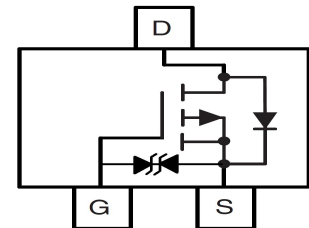


LOW VOLTAGE MOSFET (P-CHANNEL)
FEATURES

- Low on-resistance: $V_{DS}=-20V, R_{DS(ON)} \leq 92m\Omega @ V_{GS}=-10V, I_D=-2A$
- Low gate charge and ESD protection
- For Load switch applications
- Surface Mount device


SOT-23

MECHANICAL DATA

- Case: SOT-23
- Case Material: Molded Plastic. UL flammability
- Classification Rating: 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.008 grams (approximate)

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	-20	V
Gate-source voltage	V_{GS}	± 12	V
Continuous drain current ($T_J = 150^\circ\text{C}$)	I_D	$T_A = 25^\circ\text{C}$	-2
		$T_A = 70^\circ\text{C}$	-2
Pulsed drain current	I_{DM}	-17	A
Continuous Source-Drain Diode current	I_S	-1.5	A
Power dissipation	P_D	$T_A = 25^\circ\text{C}$	1.4
		$T_A = 70^\circ\text{C}$	0.9
Thermal resistance from Junction to ambient	$R_{\theta JA}$	125	$^\circ\text{C/W}$
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions	
Drain-Source breakdown voltage	$V_{(BR)DSS}^*$	-20			V	$V_{GS}=0V, I_D=-250\mu A$	
Zero gate voltage drain current	I_{DSS}^*			-1	μA	$V_{DS}=-20V, V_{GS}=0V$	
				-5	μA	$V_{DS}=-20V, V_{GS}=0V, T_J = 55^\circ\text{C}$	
Gate-body leakage current	I_{GSS}^*			± 10	μA	$V_{DS}=0V, V_{GS}=\pm 12V$	
Gate-threshold voltage	$V_{GS(th)}^*$	-0.5	-0.85	-1.2	V	$V_{DS}=V_{GS}, I_D=-250\mu A$	
On state drain current	$I_{D(ON)}^*$	-17			A	$V_{DS}=-5V, V_{GS}=-4.5V$	
Drain-source on-resistance	$R_{DS(ON)}^*$		76	92	$m\Omega$	$V_{GS}=-10V, I_D=-2A$	
				94	118	$m\Omega$	$V_{GS}=-4.5V, I_D=-2A$
				128	166	$m\Omega$	$V_{GS}=-2.5V, I_D=-1A$
Forward transconductance	g_{FS}		6.8		S	$V_{DS}=-5V, I_D=-2A$	
Gate resistance	R_g		11.2	17	Ω	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	
Input capacitance	C_{iss}	250	325	400	pF	$V_{DS}=-10V, V_{GS}=0V, f=1\text{MHz}$	
Output capacitance	C_{oss}	40	63	85	pF		
Reverse transfer capacitance	C_{rss}	22	37	52	pF		
Turn-on delay time	$t_{d(on)}$		11		nS	$V_{DS}=-10V, V_{GS}=-10V,$ $R_{GEN}=3\Omega, R_L=5\Omega$	
Turn-on rise time	t_r		5.5		nS		
Turn-off delay time	$t_{d(off)}$		22		nS		
Turn-off fall time	t_f		8		nS		
Total gate charge	Q_g		3.2	4.5	nC	$V_{DS}=-10V, V_{GS}=-4.5V, I_D=-2A$	
Gate-source charge	Q_{gs}		0.6		nC		
Gate-drain charge	Q_{gd}		0.9		nC		
Diode forward voltage	V_{SD}			-1.2	V	$I_S=-1.6A, V_{GS}=0V$	
Maximum Body-Diode Continuous Current	I_S			-1.5	A		
Body Diode Reverse Recovery Time	t_{rr}		6.1		nS	$I_F=-2A, di/dt=100A/\mu S$	
Body Diode Reverse Recovery Charge	Q_{rr}		1.4		nC	$I_F=-2A, di/dt=100A/\mu S$	

Note: 1. Pulse test ; Pulse width $\leq 300\mu s$, Duty cycle $\leq 0.5\%$.

LOW VOLTAGE MOSFET (P-CHANNEL)

Typical Characteristics

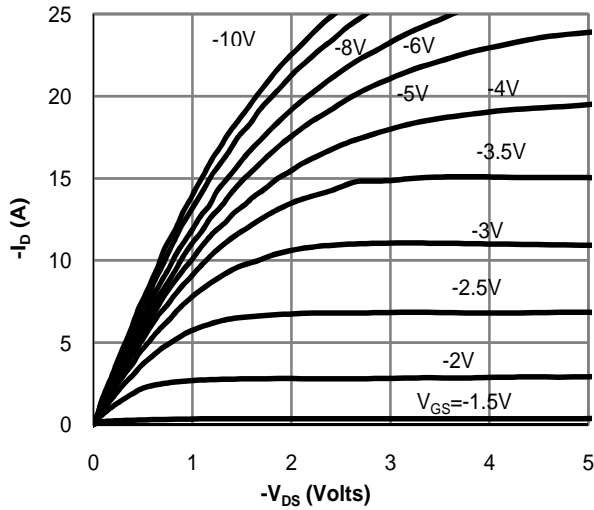


Fig 1: On-Region Characteristics

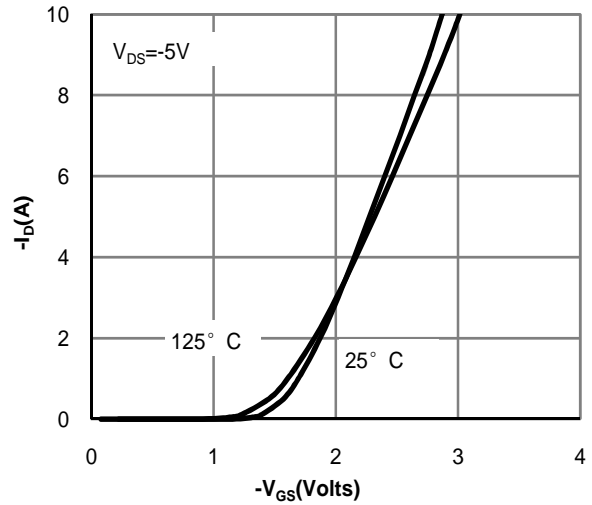


Figure 2: Transfer Characteristics

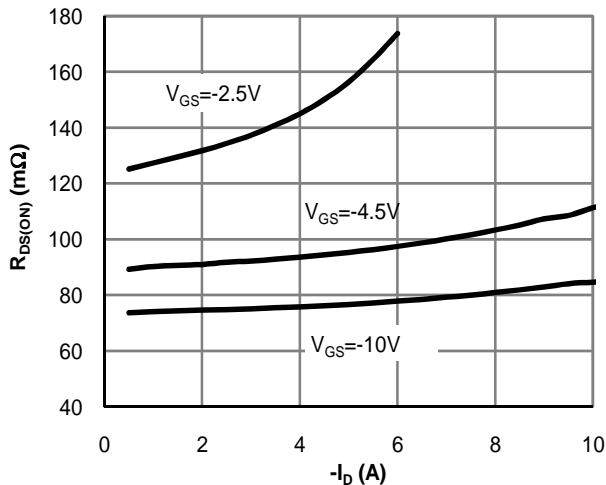


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

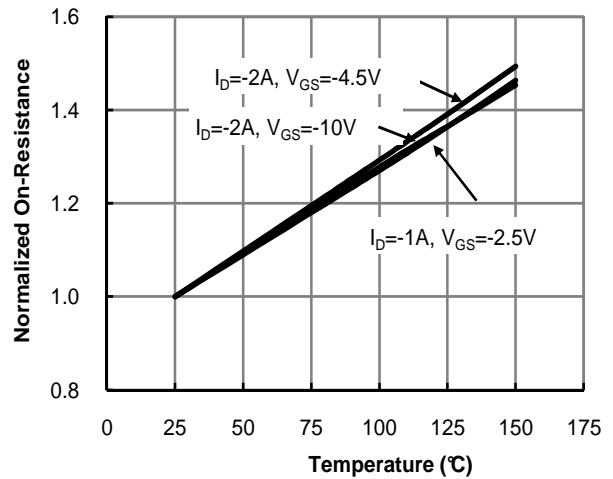


Figure 4: On-Resistance vs. Junction Temperature

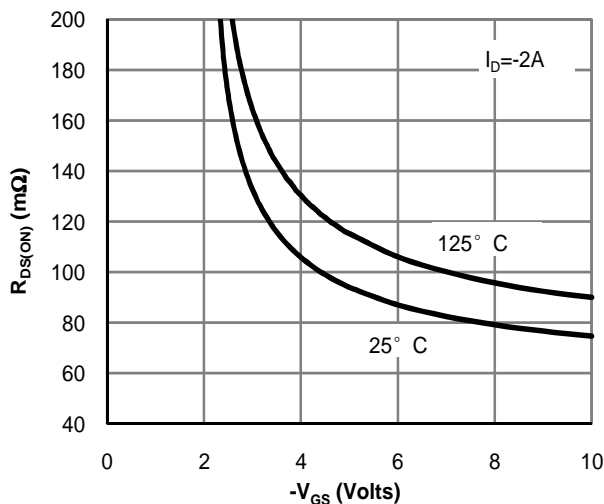


Figure 5: On-Resistance vs. Gate-Source Voltage

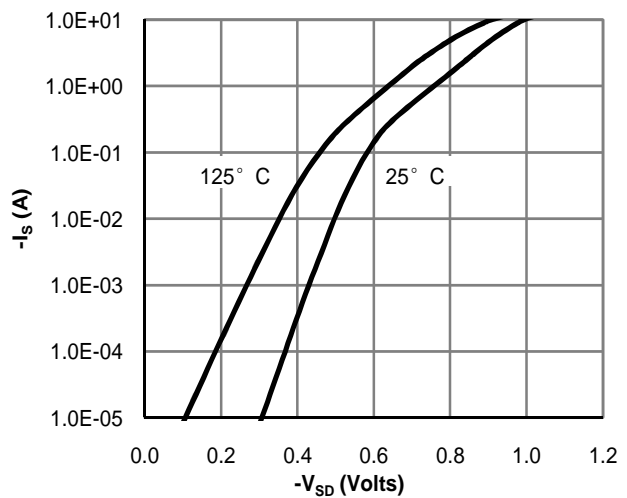


Figure 6: Body-Diode Characteristics

LOW VOLTAGE MOSFET (P-CHANNEL)

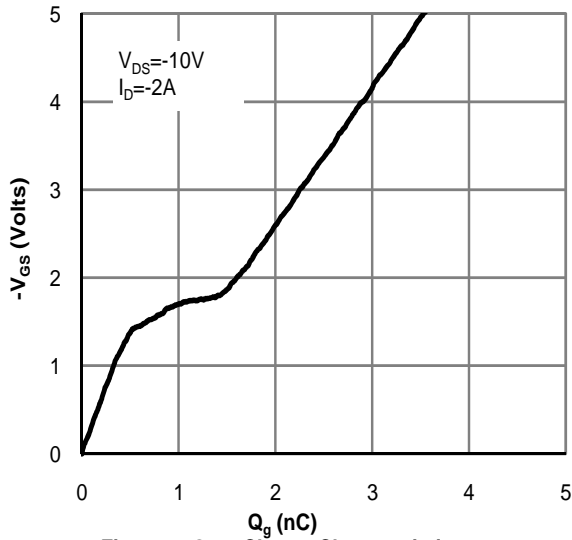


Figure 7: Gate-Charge Characteristics

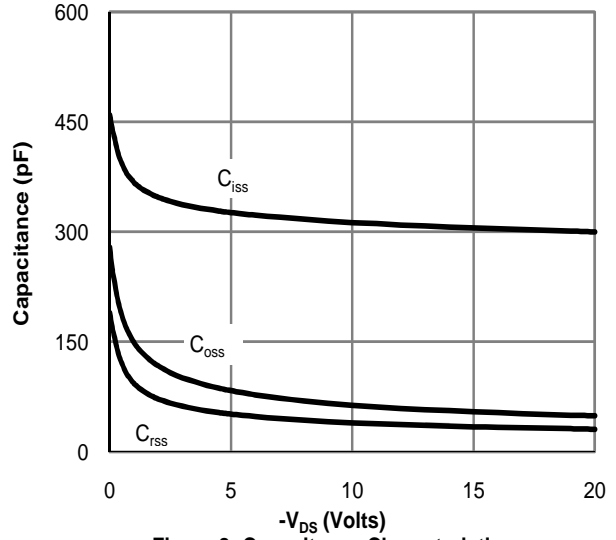


Figure 8: Capacitance Characteristics

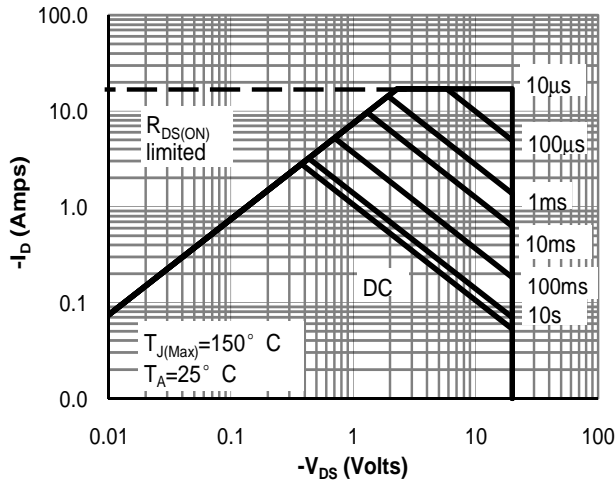


Figure 9: Maximum Forward Biased Safe Operating Area

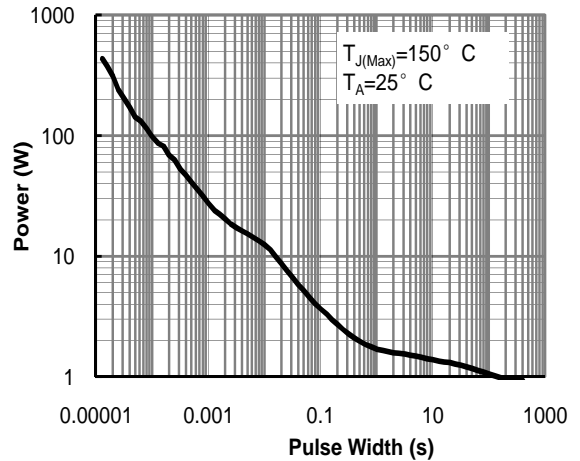


Figure 10: Single Pulse Power Rating Junction-to-Ambient

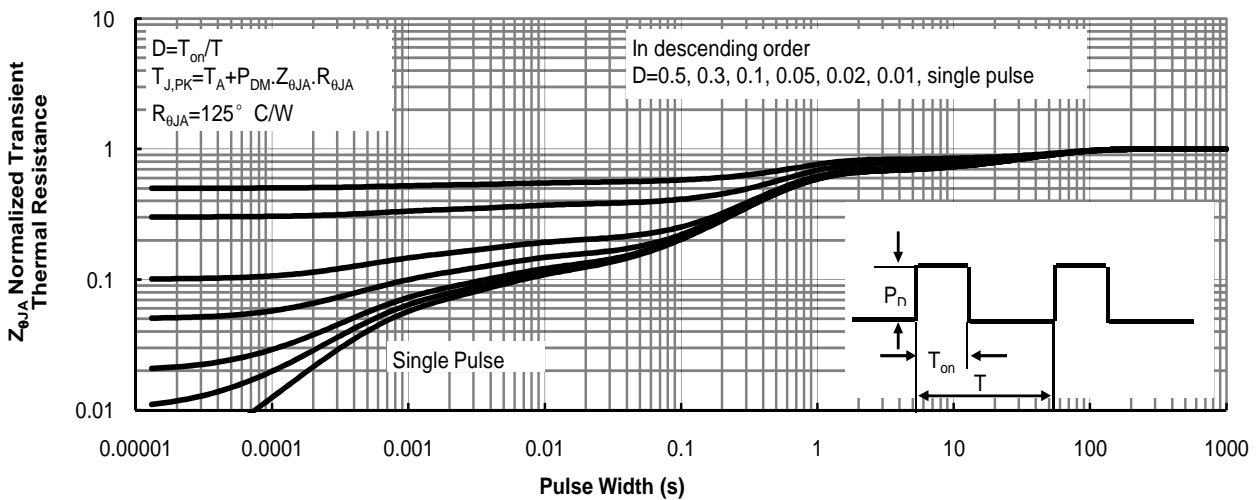
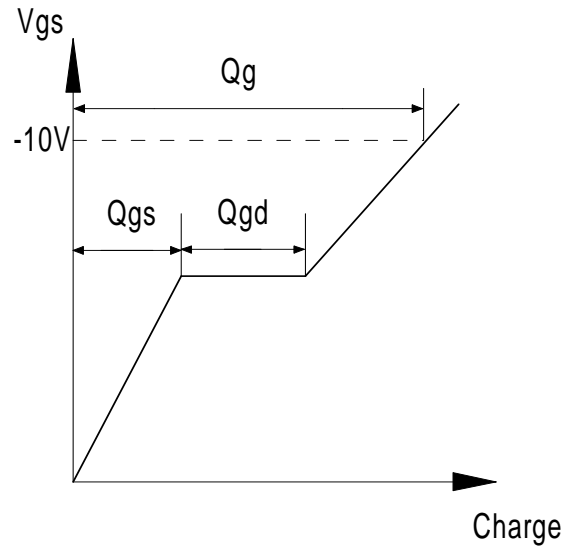
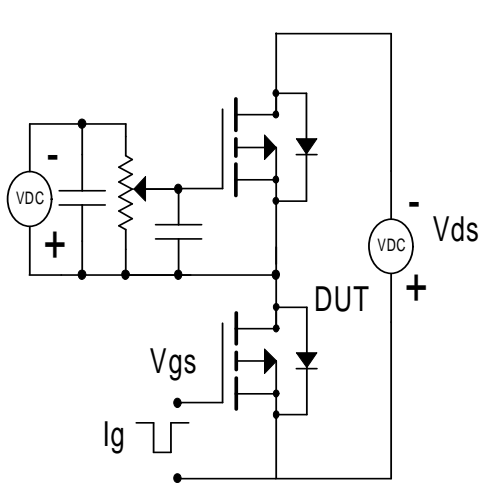


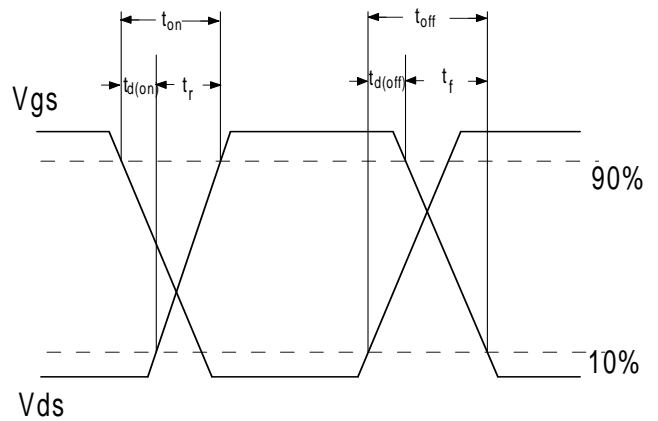
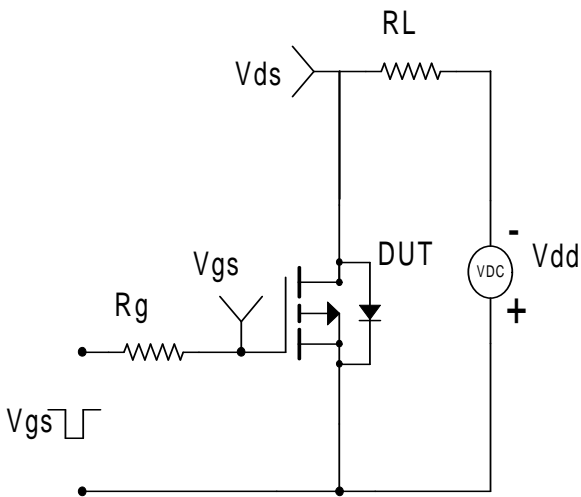
Figure 11: Normalized Maximum Transient Thermal Impedance

LOW VOLTAGE MOSFET (P-CHANNEL)

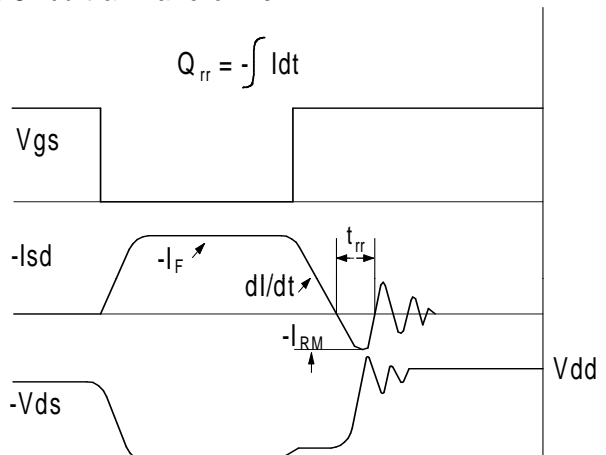
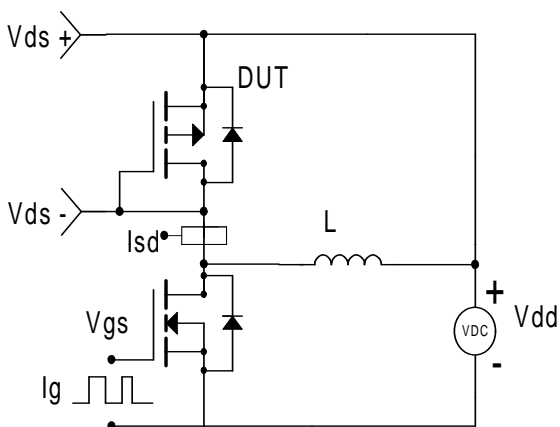
Gate Charge Test Circuit & Waveform

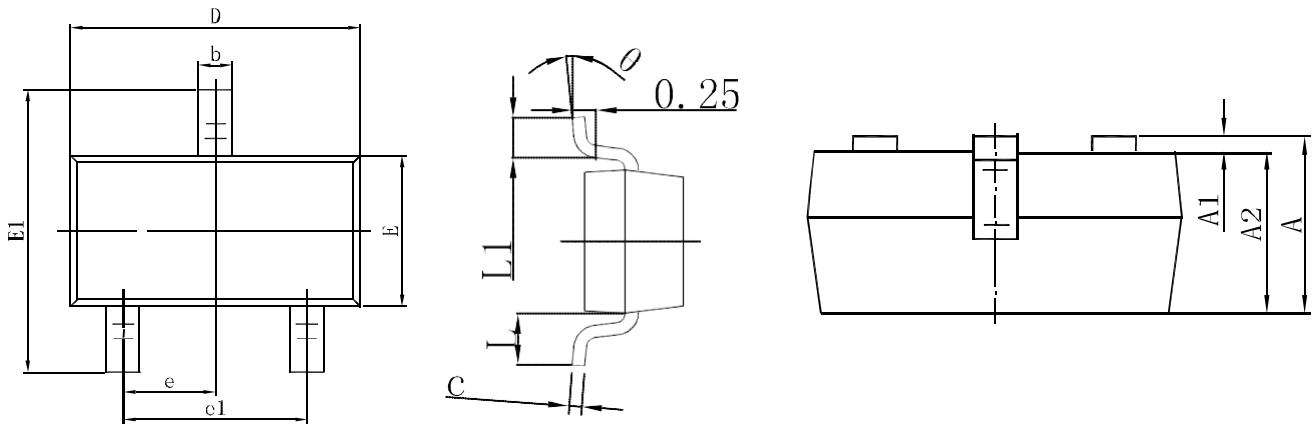


Resistive Switching Test Circuit & Waveforms

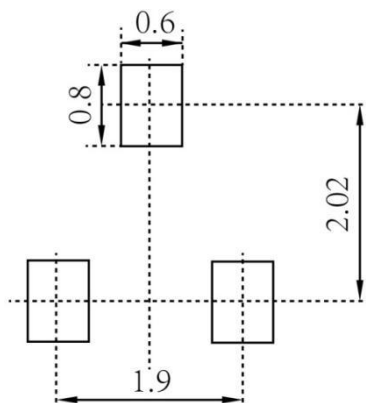


Diode Recovery Test Circuit & Waveforms



LOW VOLTAGE MOSFET (P-CHANNEL)
SOT-23 Package Outline Dimensions


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

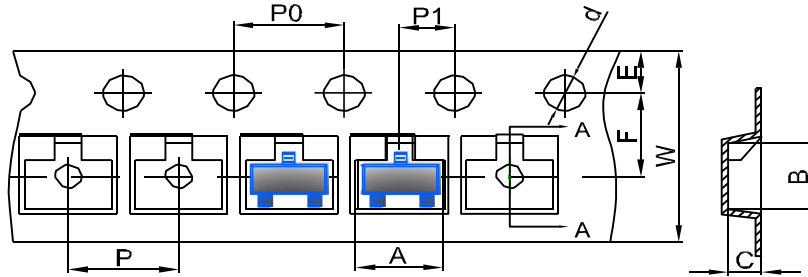
SOT-23 Suggested Pad Layout

Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only

LOW VOLTAGE MOSFET (P-CHANNEL)

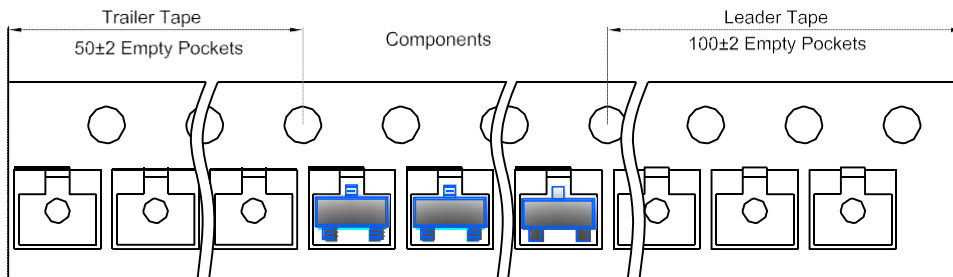
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

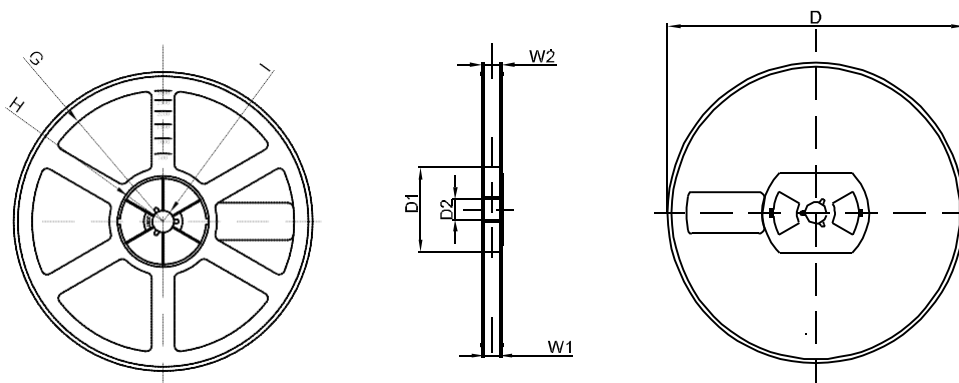


DIMENSIONS ARE IN MILLIMETER										
TYPE	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00
TOLERANCE	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1	±0.1

SOT-23 Tape Leader and Trailer



SOT-23 Reel



DIMENSIONS ARE IN MILLIMETER								
REEL OPTION	D	D1	D2	G	H	I	W1	W2
7" DIA	Ø178	54.40	13.00	R78	R25.60	R6.50	9.50	12.30
TOLERANCE	±2	±1	±1	±1	±1	±1	±1	±1